

COMPLEMENTARY PAIR ENHANCEMENT MODE MOSFET

Product Summary

Device	$V_{(BR)DSS}$	$R_{DS(ON)}$ Max	I_D $T_A = +25^\circ\text{C}$
Q1	30V	16m Ω @ $V_{GS} = 10\text{V}$	8.2A
		20m Ω @ $V_{GS} = 4.5\text{V}$	7.3A
Q2	-30V	28m Ω @ $V_{GS} = -10\text{V}$	-6.2A
		38m Ω @ $V_{GS} = -4.5\text{V}$	-5.2A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

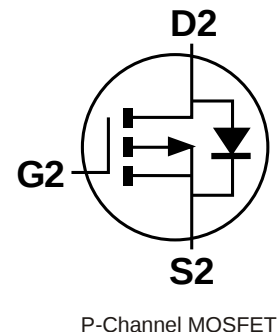
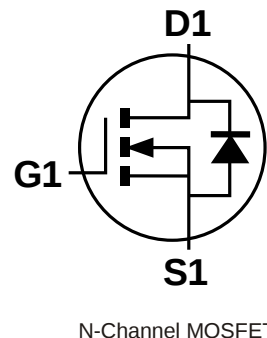
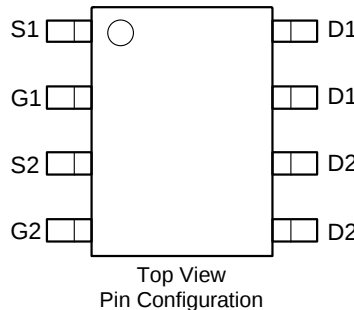
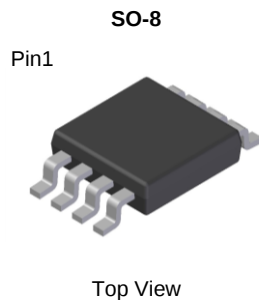
- DC-DC Converters
- Power Management Functions
- Backlighting

Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe
Solderable per MIL-STD-202, Method 208 
- Weight: 0.074 grams (Approximate)

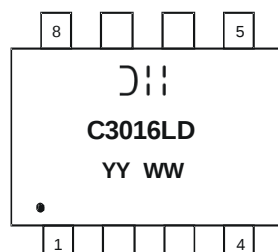


Ordering Information (Note 4)

Part Number	Case	Packaging
DMC3016LSD-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



 = Manufacturer's Marking
 C3016LD = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 15 = 2015)
 WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value Q1	Value Q2	Units
Drain-Source Voltage			V _{DSS}	30	-30	V
Gate-Source Voltage			V _{GSS}	±20	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	8.2 6.5	-6.2 -5.0	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	10.5 8.4	-8.0 -6.4	A
Maximum Body Diode Forward Current (Note 6)			I _S	2.5	-2.5	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	80	-40	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	22	-22	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	25	25	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.2	W
	T _A = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	102	°C/W
	t < 10s		62	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.6	W
	T _A = +70°C		1.0	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	78	°C/W
	t < 10s		47	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	12	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (N-Channel Q1) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1.0	—	3.0	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	12	16	mΩ	V _{GS} = 10V, I _D = 12A
		—	15	20		V _{GS} = 4.5V, I _D = 10A
Diode Forward Voltage	V _{SD}	—	0.7	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	1,415	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{OSS}	—	119	—		
Reverse Transfer Capacitance	C _{RSS}	—	82	—		
Gate Resistance	R _G	—	2.6	3.2	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _G	—	11.3	—	nC	V _{DS} = 15V, I _D = 12A
Total Gate Charge (V _{GS} = 10V)	Q _G	—	25.1	—		
Gate-Source Charge	Q _{GS}	—	3.5	—		
Gate-Drain Charge	Q _{GD}	—	3.6	—		
Turn-On Delay Time	t _{D(ON)}	—	4.8	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _L = 1.25Ω, R _G = 3Ω,
Turn-On Rise Time	t _R	—	16.5	—		
Turn-Off Delay Time	t _{D(OFF)}	—	26.1	—		
Turn-Off Fall Time	t _F	—	5.6	—		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
 - UIS in production with L = 0.1mH, starting T_A = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

Electrical Characteristics (Continued) (P-Channel Q2) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	-1.0	—	-3.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	21	28	mΩ	V _{GS} = -10V, I _D = -7A
		—	30	38		V _{GS} = -4.5V, I _D = -6.2A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -2.1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	1,241	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{OSS}	—	147	—		
Reverse Transfer Capacitance	C _{RSS}	—	110	—		
Gate Resistance	R _G	—	15	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _G	—	10.9	—	nC	V _{DS} = -15V, I _D = -7A
Total Gate Charge (V _{GS} = -10V)	Q _G	—	22	—		
Gate-Source Charge	Q _{GS}	—	3.5	—		
Gate-Drain Charge	Q _{GD}	—	4.7	—		
Turn-On Delay Time	t _{D(on)}	—	9.7	—	ns	V _{DS} = -15V, I _D = -7A V _{GS} = -10V, R _G = 6Ω
Turn-On Rise Time	t _R	—	17.1	—		
Turn-Off Delay Time	t _{D(off)}	—	60.5	—		
Turn-Off Fall Time	t _F	—	40.4	—		

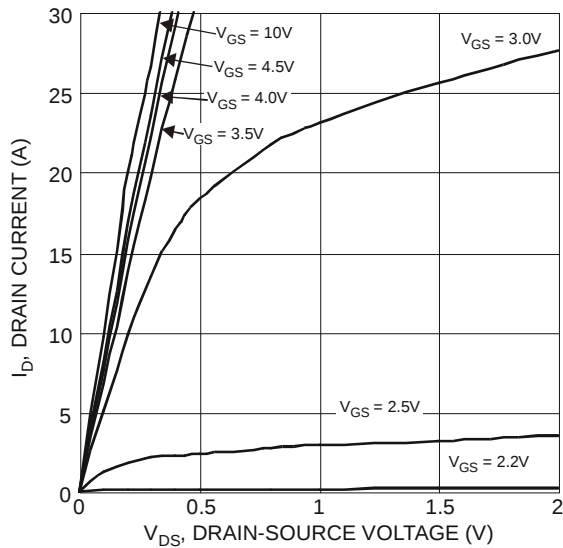


Figure 1 Typical Output Characteristics

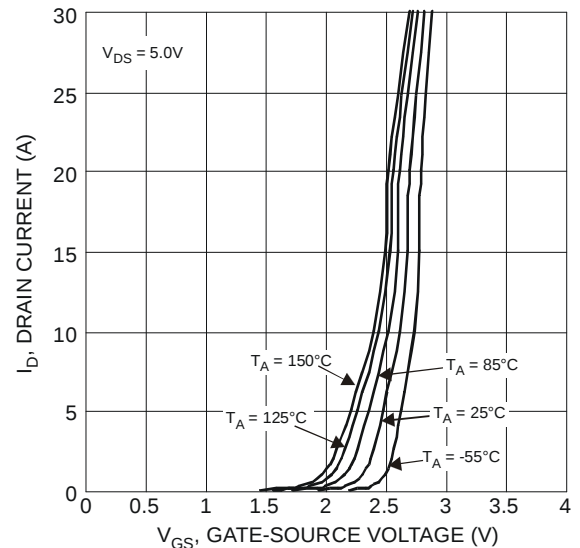


Figure 2 Typical Transfer Characteristics

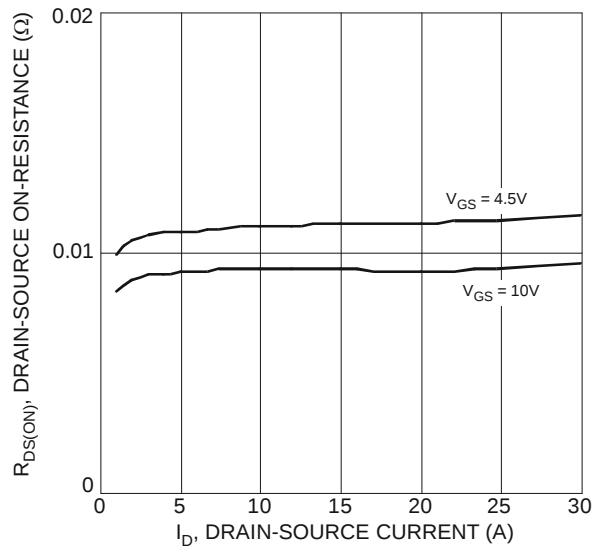


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

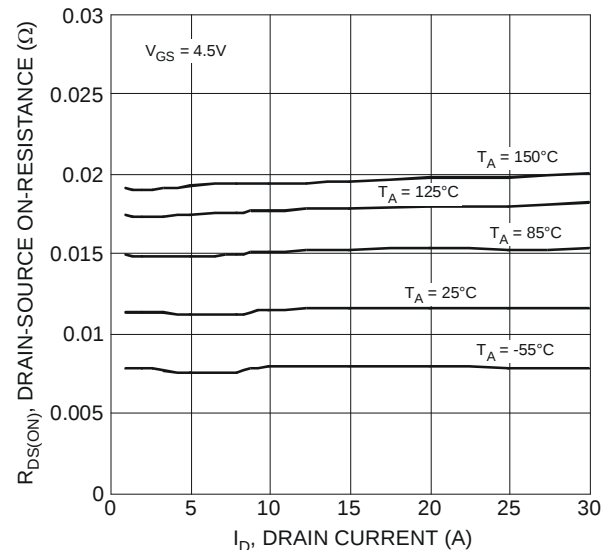


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

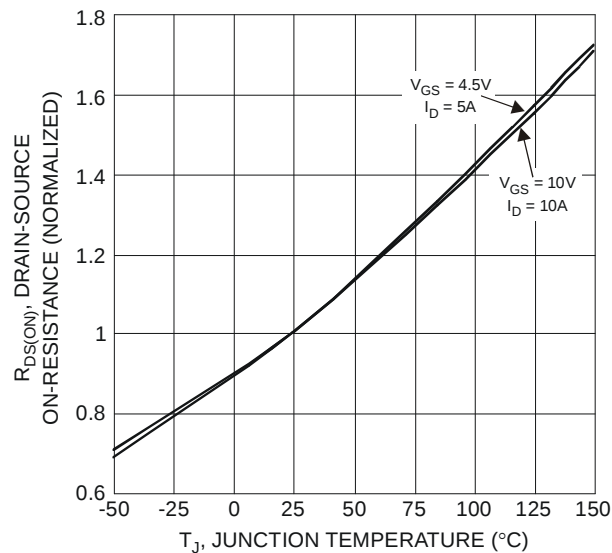


Figure 5 On-Resistance Variation with Temperature

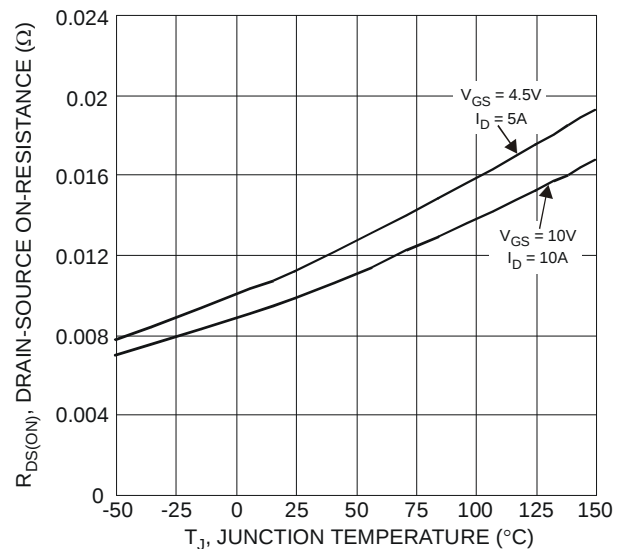


Figure 6 On-Resistance Variation with Temperature

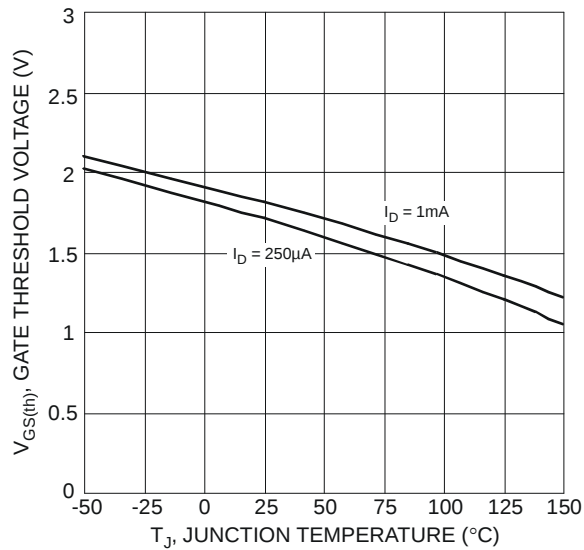


Figure 7 Gate Threshold Variation vs. Ambient Temperature

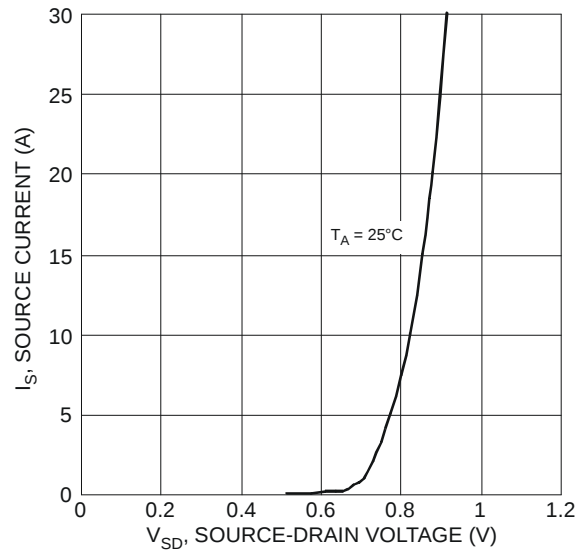


Figure 8 Diode Forward Voltage vs. Current

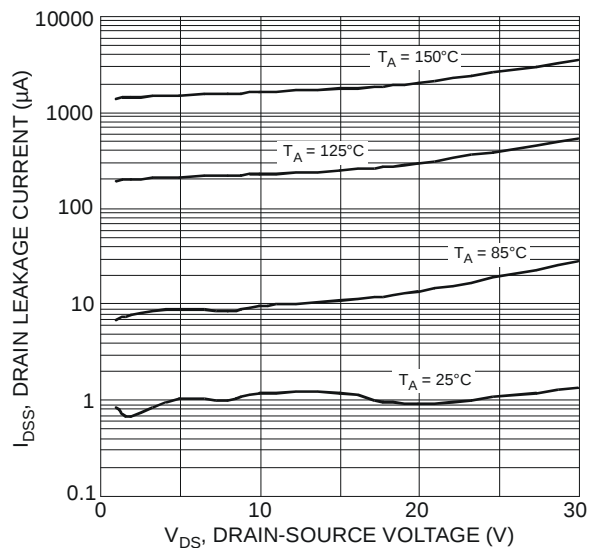


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

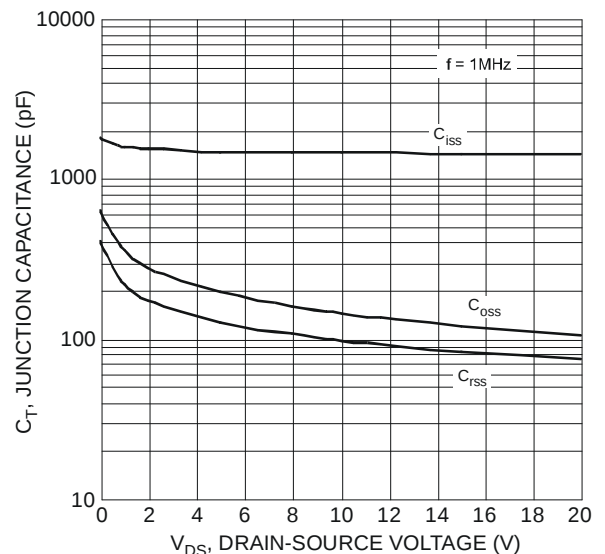


Figure 10 Typical Junction Capacitance

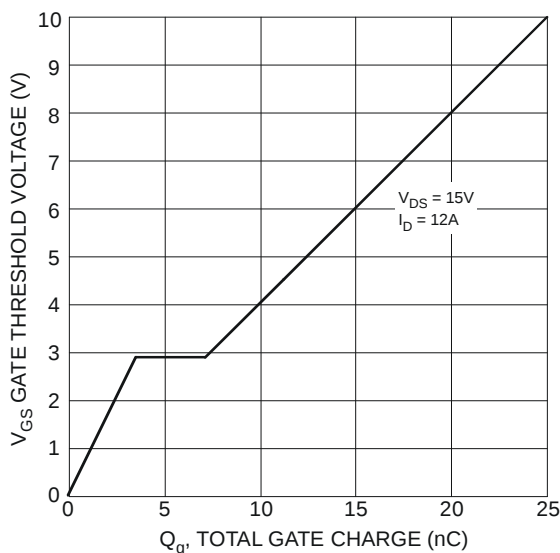


Figure 11 Gate Charge

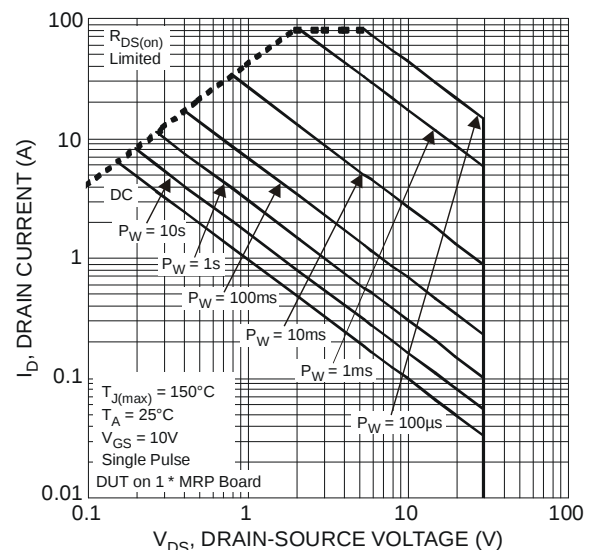


Figure 12 SOA, Safe Operation Area

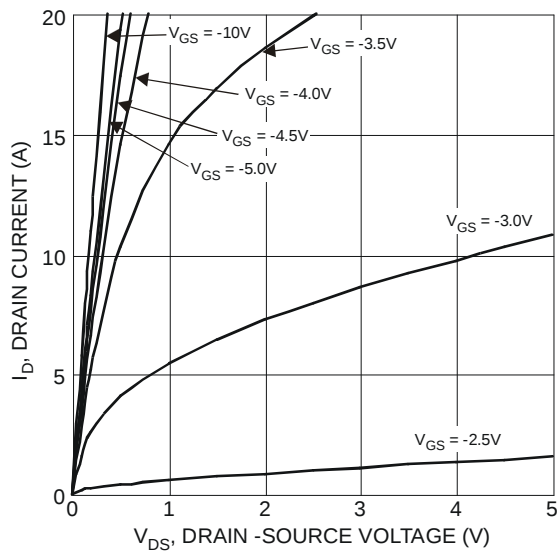


Figure 13 Typical Output Characteristics

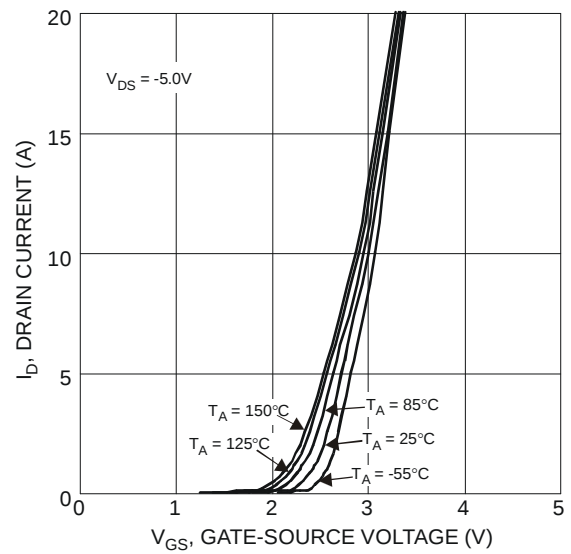


Figure 14 Typical Transfer Characteristics

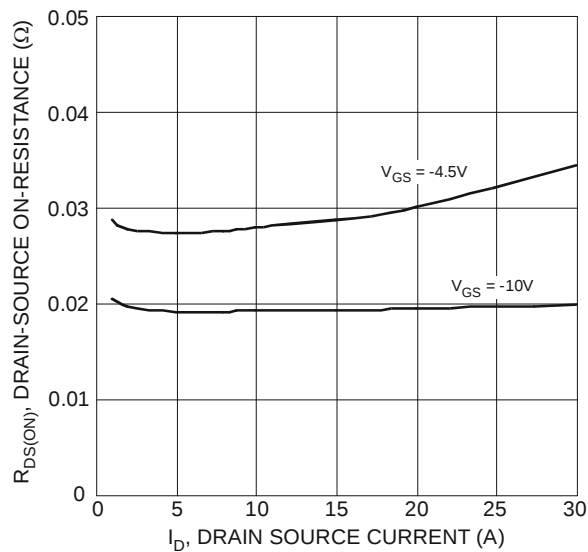


Figure 15 Typical On-Resistance vs. Drain Current and Gate Voltage

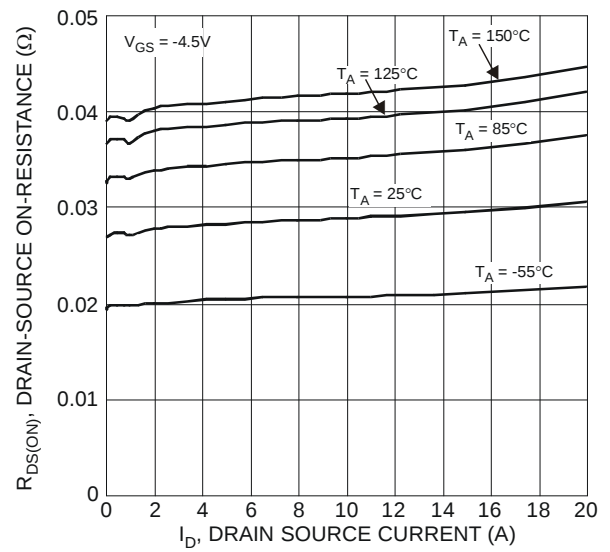


Figure 16 Typical On-Resistance vs. Drain Current and Temperature

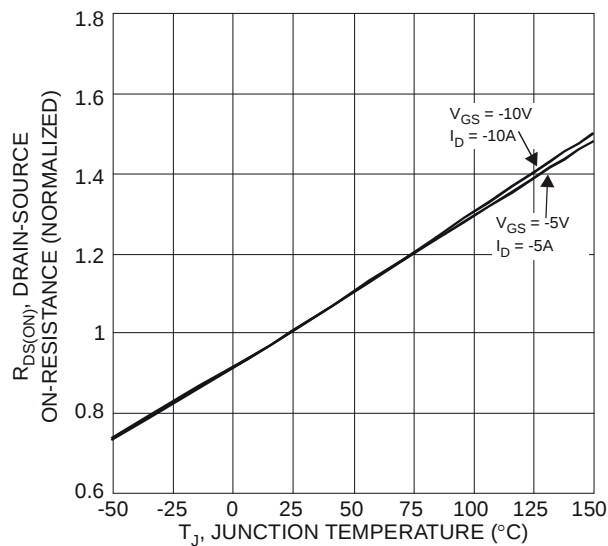


Figure 17 On-Resistance Variation with Temperature

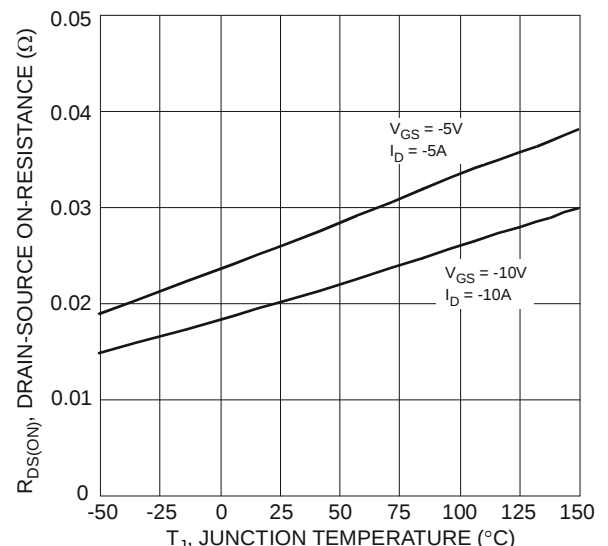


Figure 18 On-Resistance Variation with Temperature

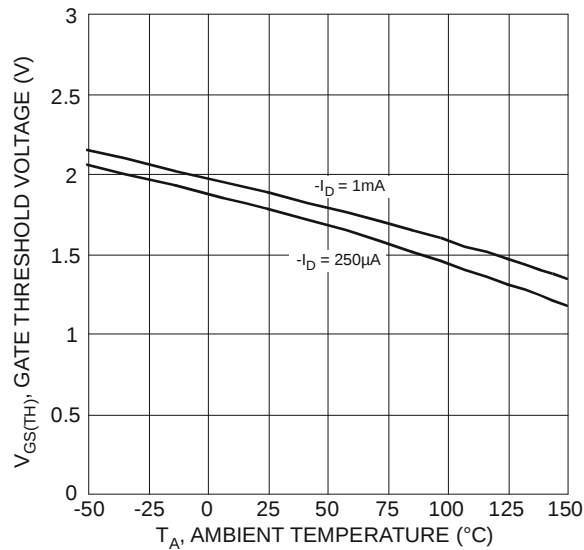


Figure 19 Gate Threshold Variation vs. Ambient Temperature

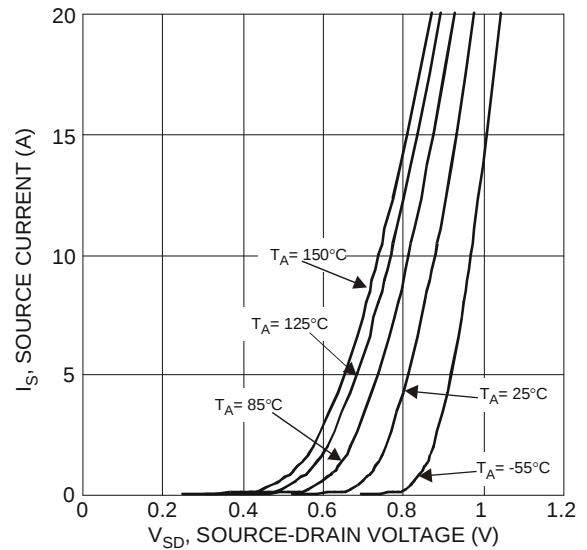


Figure 20 Diode Forward Voltage vs. Current

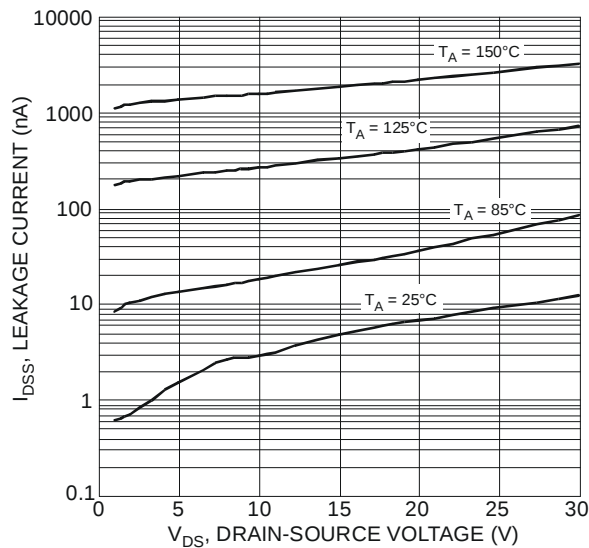


Figure 21 Typical Drain-Source Leakage Current vs. Voltage

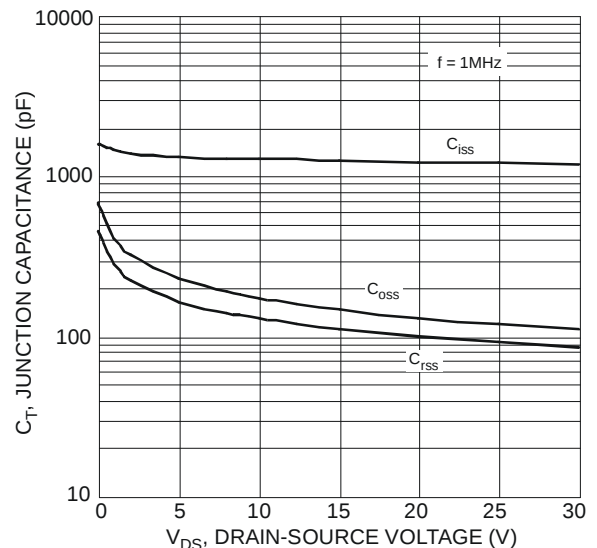


Figure 22 Typical Junction Capacitance

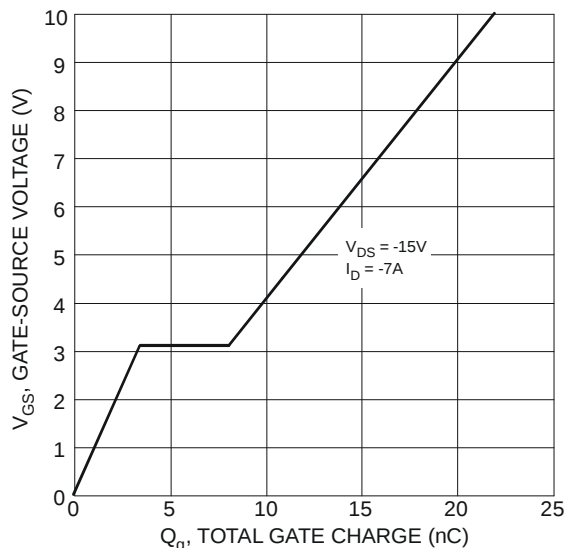


Figure 23 Gate-Charge Characteristics

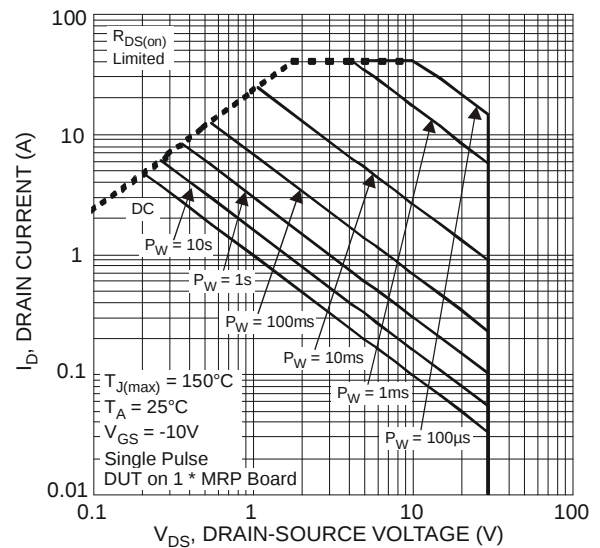
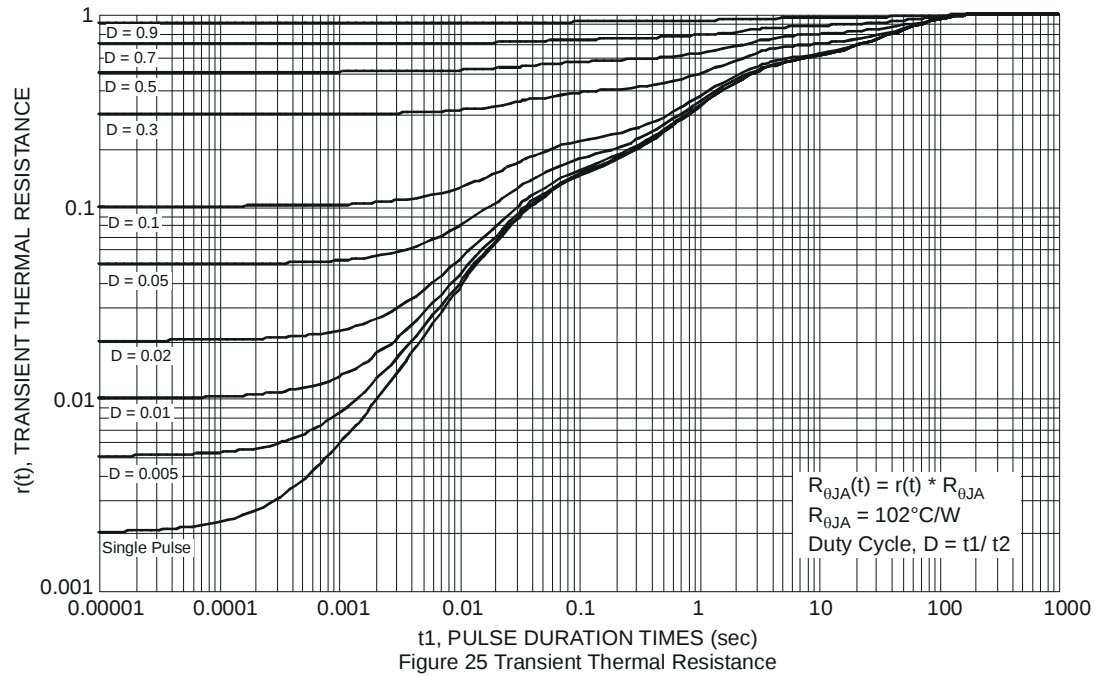


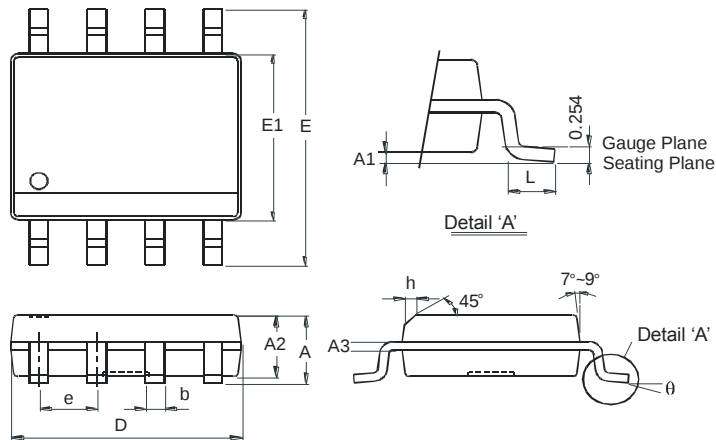
Figure 24 SOA, Safe Operation Area



Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

SO-8

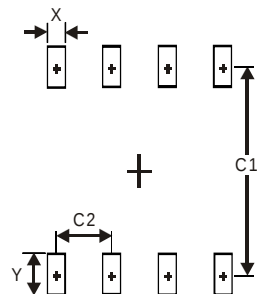


SO-8		
Dim	Min	Max
A	—	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	—	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

SO-8



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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